

**Semiconductor devices - Mechanical and climatic  
test methods - Part 34: Power cycling**

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## EESTI STANDARDI EESSÕNA

## NATIONAL FOREWORD

Käesolev Eesti standard EVS-EN 60749-34:2010 sisaldab Euroopa standardi EN 60749-34:2010 ingliskeelset teksti.

Standard on kinnitatud Eesti Standardikeskuse 31.12.2010 käskkirjaga ja jõustub sellekohase teate avaldamisel EVS Teatajas.

Euroopa standardimisorganisatsioonide poolt rahvuslikele liikmetele Euroopa standardi teksti kättesaadavaks tegemise kuupäev on 10.12.2010.

Standard on kättesaadav Eesti standardiorganisatsioonist.

This Estonian standard EVS-EN 60749-34:2010 consists of the English text of the European standard EN 60749-34:2010.

This standard is ratified with the order of Estonian Centre for Standardisation dated 31.12.2010 and is endorsed with the notification published in the official bulletin of the Estonian national standardisation organisation.

Date of Availability of the European standard text 10.12.2010.

The standard is available from Estonian standardisation organisation.

ICS 31.080.01

### Standardite reprodutseerimis- ja levitamiseõigus kuulub Eesti Standardikeskusele

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English version

**Semiconductor devices -  
Mechanical and climatic test methods -  
Part 34: Power cycling  
(IEC 60749-34:2010)**

Dispositifs à semiconducteurs -  
Méthodes d'essais mécaniques et  
climatiques -  
Partie 34: Cycles en puissance  
(CEI 60749-34:2010)

Halbleiterbauelemente -  
Mechanische und klimatische  
Prüfverfahren -  
Teil 34: Lastwechselprüfung  
(IEC 60749-34:2010)

This European Standard was approved by CENELEC on 2010-12-01. CENELEC members are bound to comply with the CEN/CENELEC Internal Regulations which stipulate the conditions for giving this European Standard the status of a national standard without any alteration.

Up-to-date lists and bibliographical references concerning such national standards may be obtained on application to the Central Secretariat or to any CENELEC member.

This European Standard exists in three official versions (English, French, German). A version in any other language made by translation under the responsibility of a CENELEC member into its own language and notified to the Central Secretariat has the same status as the official versions.

CENELEC members are the national electrotechnical committees of Austria, Belgium, Bulgaria, Croatia, Cyprus, the Czech Republic, Denmark, Estonia, Finland, France, Germany, Greece, Hungary, Iceland, Ireland, Italy, Latvia, Lithuania, Luxembourg, Malta, the Netherlands, Norway, Poland, Portugal, Romania, Slovakia, Slovenia, Spain, Sweden, Switzerland and the United Kingdom.

**CENELEC**

European Committee for Electrotechnical Standardization  
Comité Européen de Normalisation Electrotechnique  
Europäisches Komitee für Elektrotechnische Normung

**Management Centre: Avenue Marnix 17, B - 1000 Brussels**

## Foreword

The text of document 47/2068/FDIS, future edition 2 of IEC 60749-34, prepared by IEC TC 47, Semiconductor devices, was submitted to the IEC-CENELEC parallel vote and was approved by CENELEC as EN 60749-34 on 2010-12-01.

This European Standard supersedes EN 60749-34:2004.

The significant changes with respect from EN 60749-34:2004 include:

- the specification of tighter conditions for more accelerated power cycling in the wire bond fatigue mode;
- information that under harsh power cycling conditions high current densities in a thin die metalization might initiate electromigration effects close to wire bonds.

Attention is drawn to the possibility that some of the elements of this document may be the subject of patent rights. CEN and CENELEC shall not be held responsible for identifying any or all such patent rights.

The following dates were fixed:

- latest date by which the EN has to be implemented at national level by publication of an identical national standard or by endorsement (dop) 2011-09-01
- latest date by which the national standards conflicting with the EN have to be withdrawn (dow) 2013-12-01

Annex ZA has been added by CENELEC.

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## Endorsement notice

The text of the International Standard IEC 60749-34:2010 was approved by CENELEC as a European Standard without any modification.

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## Annex ZA (normative)

### Normative references to international publications with their corresponding European publications

The following referenced documents are indispensable for the application of this document. For dated references, only the edition cited applies. For undated references, the latest edition of the referenced document (including any amendments) applies.

NOTE When an international publication has been modified by common modifications, indicated by (mod), the relevant EN/HD applies.

<u>Publication</u>	<u>Year</u>	<u>Title</u>	<u>EN/HD</u>	<u>Year</u>
IEC 60747-1	2006	Semiconductor devices - Part 1: General	-	-
IEC 60747-2	2000	Semiconductor devices - Discrete devices and- integrated circuits - Part 2: Rectifier diodes	-	-
IEC 60747-6	2000	Semi conductor devices - Part 6: Thyristors	-	-
IEC 60749-3	-	Semiconductor devices - Mechanical and climatic test methods - Part 3: External visual examination	EN 60749-3	-
IEC 60749-23	-	Semiconductor devices - Mechanical and climatic test methods - Part 23: High temperature operating life	EN 60749-23	-

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# SEMICONDUCTOR DEVICES – MECHANICAL AND CLIMATIC TEST METHODS –

## Part 34: Power cycling

### 1 Scope and object

This part of IEC 60749 describes a test method used to determine the resistance of a semiconductor device to thermal and mechanical stresses due to cycling the power dissipation of the internal semiconductor die and internal connectors. This happens when low-voltage operating biases for forward conduction (load currents) are periodically applied and removed, causing rapid changes of temperature. The power cycling test is intended to simulate typical applications in power electronics and is complementary to high temperature operating life (see IEC 60749-23). Exposure to this test may not induce the same failure mechanisms as exposure to air-to-air temperature cycling, or to rapid change of temperature using the two-fluid-baths method. This test causes wear-out and is considered destructive.

NOTE It is not the intention of this specification to provide prediction models for lifetime evaluation.

### 2 Normative references

The following referenced documents are indispensable for the application of this document. For dated references, only the edition cited applies. For undated references, the latest edition of the referenced document (including any amendments) applies.

IEC 60747-1:2006, *Semiconductor devices – Part 1: General*

IEC 60747-2:2000, *Semiconductor devices – Discrete devices and integrated circuits – Part 2: Rectifier diodes*

IEC 60747-6:2000, *Semiconductor devices – Part 6: Thyristors*

IEC 60749-3, *Semiconductor devices – Mechanical and climatic test methods – Part 3: External visual examination*

IEC 60749-23, *Semiconductor devices – Mechanical and climatic test methods – Part 23: High temperature operating life*

### 3 Terms and definitions

For the purposes of this document the following terms and definitions apply.

NOTE Further terms and definitions concerning semi-conductor devices are contained in the IEC 60747 and IEC 60748 series.

#### 3.1

##### load current

current to which the devices are subjected to produce power loss  $P$

#### 3.2

##### case temperature

$T_c$

temperature of the base of the device under test facing the heat sink